



60V N-CHANNEL SELF PROTECTED ENHANCEMENT MODE INTELLIFET® MOSFET

Features and Benefits

Overcurrent Protection

Input Protection (ESD)

Mechanical Data

Case: SO-8

Logic Level Input (3.3V and 5V)

High Continuous Current Rating

Short Circuit Protection with Auto Restart Overvoltage Protection (active clamp) Thermal Shutdown with Auto Restart

Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)

Halogen and Antimony Free. "Green" Device (Note 3)

Case Material: Molded Plastic, "Green" Molding Compound

UL Flammability Classification Rating 94V-0 Moisture Sensitivity: Level 1 per J-STD-020

Terminals: Matte Tin Finish @3

Weight: 80.2 mg (Approximate)

Low Input Current

Product Summary

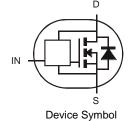
•	Continuous Drain Source Voltage	60V
•	On-State Resistance	$500 m\Omega$
•	Nominal Load Current (V _{IN} = 5V)	1.3A
	Clamping Energy	120mJ

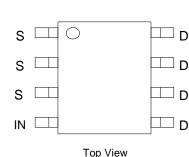
Description

The ZXMS6004N8 is a self-protected low side MOSFET with logic level input. It integrates over-temperature, overcurrent, overvoltage (active clamp) and ESD protected logic level functionality. The ZXMS6004N8 is ideal as a general purpose switch driven from 3.3V or 5V microcontrollers in harsh environments where standard MOSFETs are not rugged enough.

Applications

- Especially suited for loads with a high in-rush current such as lamps and motors
- All types of resistive, inductive and capacitive loads in switching applications
- μC compatible power switch for 12V and 24V DC applications.
- · Replaces electromechanical relays and discrete circuits
- Linear Mode capability the current-limiting protection circuitry is
 designed to de-activate at low V_{DS} to minimize on state power
 dissipation. The maximum DC operating current is therefore
 determined by the thermal capability of the package/board
 combination, rather than by the protection circuitry. This does not
 compromise the product's ability to self-protect at low V_{DS}.





Pin Out

SO-8

Top View

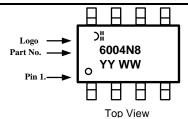
Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMS6004N8-13	6004N8	13	12	2,500 units

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU.

- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



6004N8 = Product Name YY: Year

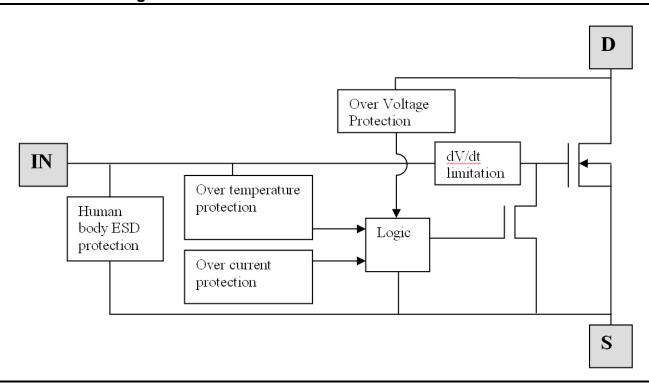
WW: Week: 01~52;

52 represents 52 and 53 week

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Functional Block Diagram



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise stated.)

Characteristic	Symbol	Value	Units
Continuous Drain-Source Voltage	V _{DS}	60	V
Drain-Source Voltage for Short Circuit Protection	V _{DS(SC)}	36	V
Continuous Input Voltage	V _{IN}	-0.5 to +6	V
Continuous Input Current @-0.2V \leq V _{IN} \leq 6V Continuous Input Current @V _{IN} $<$ -0.2V or V _{IN} $>$ 6V	lin	No limit │ I _{IN} │ ≤2	mA
Pulsed Drain Current @V _{IN} = 3.3V	I _{DM}	2	Α
Pulsed Drain Current @V _{IN} = 5V	I _{DM}	2.5	Α
Continuous Source Current (Body Diode) (Note 5)	I _S	1	Α
Pulsed Source Current (Body Diode)	I _{SM}	5	Α
Unclamped Single Pulse Inductive Energy, T _J = +25°C, I _D = 0.5A, V _{DD} = 24V	E _{AS}	120	mJ
Electrostatic Discharge (Human Body Model)	V нвм	4,000	V
Charged Device Model	V _{CDM}	1,000	V

Thermal Resistance ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Power Dissipation at $T_A = +25^{\circ}C$ (Note 5) Linear Derating Factor	P _D	1.28 10	W mW/°C
Power Dissipation at T _A = +25°C (Note 6) Linear Derating Factor	P _D	1.65 12.4	W mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	R _{0JA}	98	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R _{0JA}	76	°C/W
Thermal Resistance, Junction to Case (Note 7)	R _{θJC}	12	°C/W
Operating Temperature Range	T _J ,	-40 to +150	°C
Storage Temperature Range	T _{STG}	-55 to +150	°C

 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. Notes:

^{7.} Thermal resistance between junction and the mounting surfaces of drain and source pins.

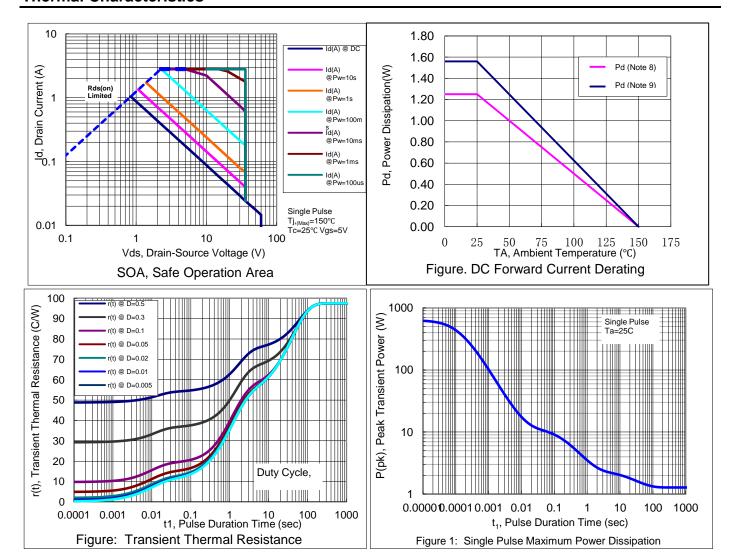


Recommended Operating Conditions

The ZXMS6004N8 s optimized for use with μC operating from 3.3V and 5V supplies.

Characteristic	Symbol	Min	Max	Unit
Input Voltage Range	V _{IN}	0	5.5	V
Ambient Temperature Range	T _A	-40	+125	°C
High Level Input Voltage for MOSFET to be on	V _{IH}	3	5.5	V
Low Level Input Voltage for MOSFET to be off	V _{IL}	0	0.7	V
Peripheral Supply Voltage (voltage to which load is referred)	V _P	0	36	V

Thermal Characteristics



Note:

- 8. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout
- 9. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.



Electrical Characteristics (@T_A = +25°C, unless otherwise stated.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Static Characteristics						
Drain-Source Clamp Voltage	V _{DS(AZ)}	60	65	70	V	$I_D = 10 \text{mA}$
Off State Drain Current		-	_	0.5		$V_{DS} = 12V, V_{IN} = 0V$
On State Drain Current	I _{DSS}	-	_	1	μΑ	$V_{DS} = 36V, V_{IN} = 0V$
Input Threshold Voltage	$V_{IN(th)}$	0.7	1	1.5	V	$V_{DS} = V_{GS}$, $I_D = 1mA$
Input Current	Los	-	60	100		$V_{IN} = +3V$
Imput Current	I _{IN}	-	120	200	μΑ	$V_{IN} = +5V$
Input Current While Over-Temperature Active	_	-	_	400	μA	$V_{IN} = +5V$
Static Drain-Source On-State Resistance)	-	400	600	mΩ	$V_{IN} = +3V, I_D = 0.5A$
Static Diani-Source On-State Resistance	R _{DS(on)}	-	350	500	111122	$V_{IN} = +5V, I_D = 0.5A$
Continuous Drain Current (Note 5)	I _D	0.9	_	_		$V_{IN} = 3V; T_A = +25^{\circ}C$
Continuous Drain Current (Note 5)		1.0	-	_	A	$V_{IN} = 5V; T_A = +25^{\circ}C$
Continuous Drain Current (Note 6)		1.2	_	_		$V_{IN} = 3V; T_A = +25^{\circ}C$
Continuous Diain Current (Note 6)		1.3	_	_		$V_{IN} = 5V$; $T_A = +25$ °C
Current Limit (Note 10)	I _{D(LIM)}	0.7	1.7	_	A	V _{IN} = +3V
Current Limit (Note 10)		1	2.2	_		$V_{IN} = +5V$
Dynamic Characteristics						•
Turn On Delay Time	t _{d(on)}	-	5	_		$V_{DD} = 12V$, $I_D = 0.5A$, $V_{GS} = 5V$
Rise Time	tr	-	10	_		
Turn Off Delay Time	t _{d(off)}	-	45	_	μs	
Fall Time	t _f	-	15	_		
Over-Temperature Protection						
Thermal Overload Trip Temperature (Note 11)	T_{JT}	150	+175	-	°C	
Thermal Hysteresis (Note 11)	ΔT_{JT}	-	+10	-	°C	

Notes:

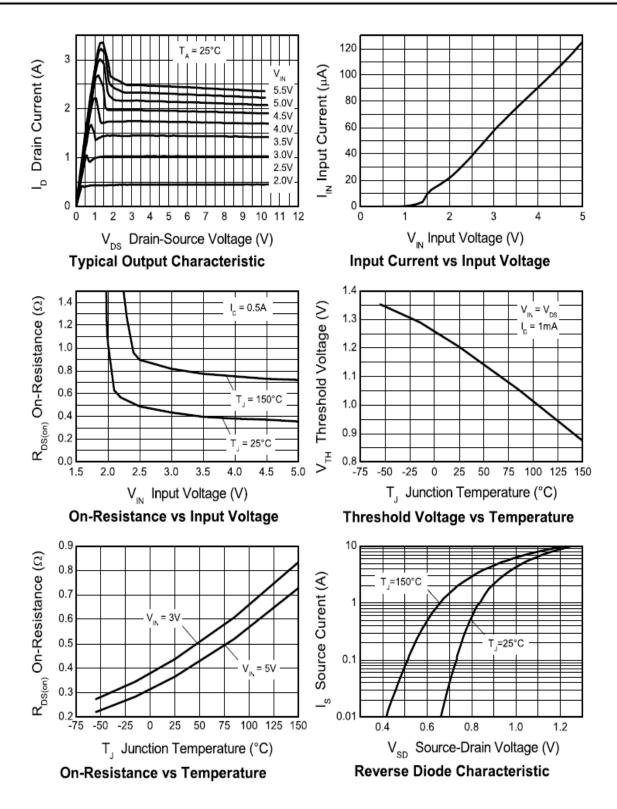
^{10.} The drain current is restricted only when the device is in saturation (see graph 'typical output characteristic'). This allows the device to be used in the fully on state without interference from the current limit. The device is fully protected at all drain currents, as the low power dissipation generated outside saturation makes current limit unnecessary.

11. Over-temperature protection is designed to prevent device destruction under fault conditions. Fault conditions are considered as "outside" normal

operating range, so this part is not designed to withstand over-temperature for extended periods.

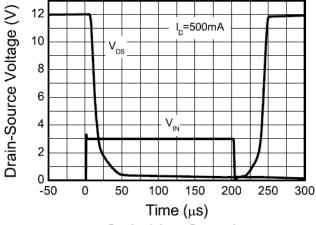


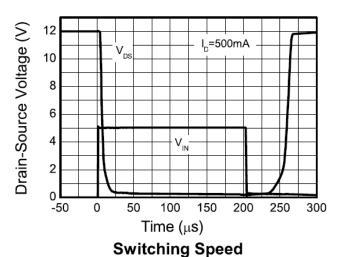
Typical Characteristics



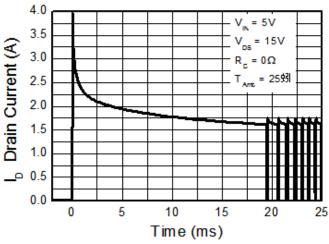


Typical Characteristics (continued)





Switching Speed

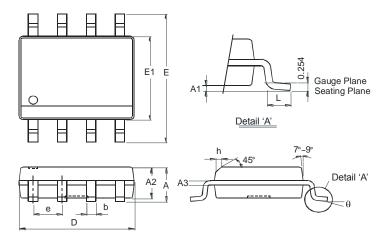


Typical Short Circuit Protection



Package Outline Dimensions

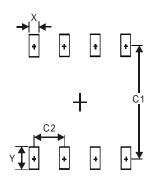
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SO-8				
Dim	Min	Max		
Α	-	1.75		
A1	0.10	0.20		
A2	1.30	1.50		
A3	0.15	0.25		
b	0.3	0.5		
D	4.85	4.95		
Е	5.90	6.10		
E1	3.85	3.95		
е	1.27 Typ			
h	-	0.35		
L	0.62	0.82		
θ	0°	8°		
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Χ	0.60
Y	1.55
C1	5.4
C2	1.27



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